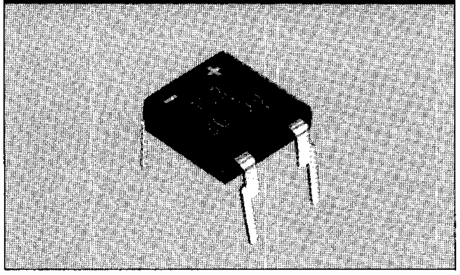
CAT. No. J469-1

SHINDENGEN

Silicon Rectifier Diode

S1NB

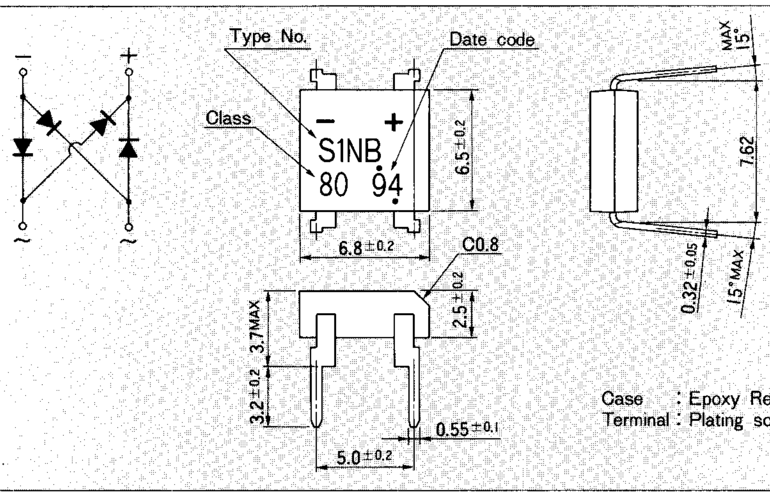
1A 100~800V



THE ADVANCED 1 AMPERE RECTIFIER DIODES ON THE MARKET TODAY

Compact And Lightweight Construction With Superior Current Characteristics.

■ OUTLINE DIMENSIONS



Case : Epoxy Resin (Black) UL94 94V-0
Terminal : Plating solder

[Unit : mm]

■ FEATURES

- Glass passivated chip.
- Smallest size and lightest weight 1 Amp. rated bridge diodes.
- Stick packages are available for automated assembly machine.

■ RATINGS

Absolute Maximum Ratings

Item	Symbol	Conditions / Type No.	S1NB 10	S1NB 20	S1NB 40	S1NB 60	S1NB 80	Unit
Storage Temperature	Tstg		−40~150					℃
Operating Junction Temperature	Tj		150					℃
Maximum Reverse Voltage	V_{RM}		100	200	400	600	800	V
Average Rectified Forward Current	Io	50Hz sine wave, Resistive load, Ta=25℃, On P.C.B.	1					A
Peak Surge Forward Current	I_{FSM}	50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=25℃	30					A

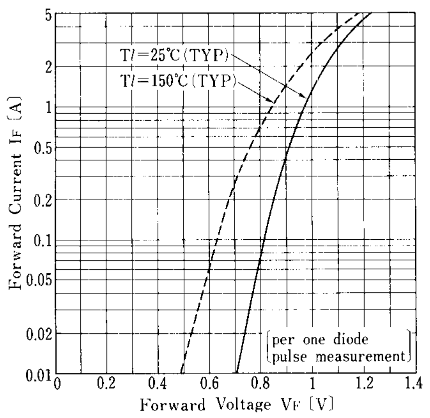
Electrical Characteristics (T*l*=25℃)

Item	Symbol	Conditions	S1NB 10	S1NB 20	S1NB 40	S1NB 60	S1NB 80	Unit
Forward Voltage	V_F	I_F=0.5A, Pulse measurement, Rating of per diode	MAX 1.05					V
Reverse Current	I_R	V_R=V_{RM}, Pulse measurement, Rating of per diode	MAX 10				MAX 20	μA
Thermal Resistance	θjl	Between junction and lead	MAX 15					℃/W
	θja	Between junction and ambient	MAX 68					

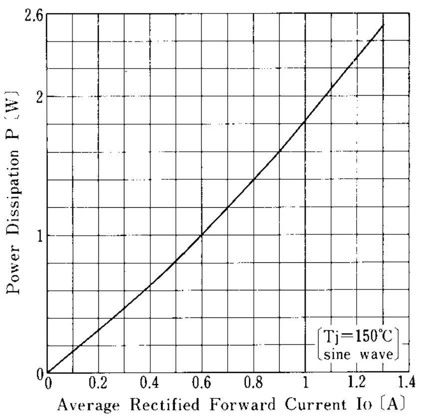
Shindengen

■ CHARACTERISTIC DIAGRAMS

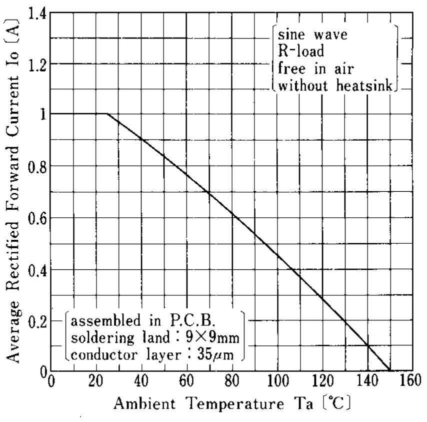
Forward Voltage



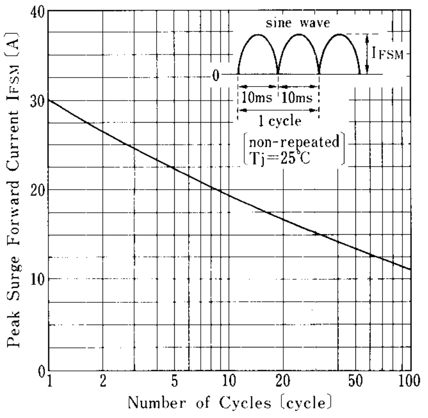
Power Dissipation



Derating Curve Ta-Io



Surge Forward Current Capability



● Note : All specifications are subject to change without notice.

SHINDENGEN
ELECTRIC MFG. CO., LTD.

New-Ohtemachi Bldg.,2-1, 2-chome Ohtemachi
Chiyoda-ku, Tokyo 100, Japan
Phone : Tokyo (03) 279—4432
Telex : 222—2539 DENGEN J
Fax : (03) 279—6478